

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

Claim 1 (Currently Amended): A display device comprising:
a pair of substrates;
an active matrix circuit and a driver circuit provided on one of the pair of the substrates;
and
a sealing member formed ~~on said one of the pair of the substrates~~ so as to cover the driver circuit, the sealing member being capable of light blocking; and
an orientating film formed on said sealing member,
wherein said sealing member comprises a pigment for light blocking.

Claim 2 (Previously Presented): A display device according to claim 1,
wherein the active matrix circuit has pixels arranged in a matrix form, and
wherein regions in each of the pixels where source lines and dram lines overlap with a pixel electrode form a black matrix.

Claim 3 (Previously Presented): A display device according to claim 1,
wherein one of an electrode or a wiring line connected to a source or drain of a thin-film transistor formed in the active matrix circuit is one of a metal film, a semiconductor film, and a silicide film; and
wherein a light blocking film for the thin-film transistor is formed by using the one of the metal film, the semiconductor film, 0and the silicide film.

Claim 4 (Previously Presented): A display device according to claim 1, wherein said pair of the substrates are glass substrates or quartz substrates.

Claim 5 (Previously Presented): A display device according to claim 1 wherein said pair of the substrates are bonded to each other with the sealing member.

Claim 6 (Previously Presented): A device according to claim 1 further comprising:
at least a CMOS transistor formed in the driver circuit region, said CMOS transistor having an n-channel thin film transistor and a p-channel thin film transistor;
a thin film transistor formed in each pixel in the active matrix circuit, said thin film transistor having at least an active layer, a gate insulating film adjacent to said active layer, a gate electrode adjacent to said gate insulating film,
wherein a light block film is formed over said gate electrode.

Claim 7 (Previously Presented): A device according to claim 1 further comprising a liquid crystal material interposed between the pair of substrates,
wherein said sealing member seals the liquid crystal material.

Claim 8 (Currently Amended): An electronic device comprising:
at least a first substrate and a second substrate;
a driver circuit region formed on said first substrate, said ~~[[driver]]~~ driver circuit region having at least one of a shift register circuit, a NAND circuit, a level shifter circuit ~~[[or]]~~ and a buffer circuit;
an active matrix region formed on said first substrate, said active matrix region having at least a pixel;
a sealing member formed between said first and second substrates, said sealing member bonding said first and second substrates and covering said driver circuit region; and
an orientating film formed on said sealing member,

wherein said sealing member shields said driver circuit region from light; and
wherein said sealing member comprises a pigment for light blocking.

Claim 9 (Canceled)

Claim 10 (Previously Presented): A device according to claim 8 wherein said shift register circuit comprises at least a clocked inverter and an inverter.

Claim 11 (Previously Presented): A device according to claim 8 further comprising:
at least a CMOS transistor formed in said driver circuit region, said CMOS transistor having an n-channel thin film transistor and a p-channel thin film transistor;
a thin film transistor formed in said pixel, said thin film transistor having at least an active layer, a gate insulating film adjacent to said active layer, a gate electrode adjacent to said gate insulating film, and further comprising a light blocking film formed over said gate electrode.

Claims 12-14 (Canceled)

Claim 15 (Previously Presented): A device according to claim 8 further comprising a liquid crystal material injected between the first substrate and the second substrate.

Claim 16 (Currently Amended): A display device comprising:
at least a first substrate and a second substrate;
a driver circuit region formed on said first substrate, said driver circuit region having at least one of a shift register circuit, a NAND circuit, a level shifter circuit [[or]] and a buffer circuit, wherein at least a CMOS transistor is formed in said driver circuit region, said CMOS transistor having an n-channel thin film transistor and a first p-channel thin film transistor;
an active matrix region formed on said first substrate, said active matrix region having at least a pixel, wherein a second p-channel thin film transistor is formed in said pixel; and

a sealing member formed between said first and second substrates, said sealing member bonding said first and second substrates and covering said driver circuit region[~~;~~ and,] wherein said sealing member comprises a pigment for light blocking and ~~wherein said sealing member shields said driver circuit region from light,~~

wherein said first p-channel thin film transistor comprises:

a first source region and a first drain region formed over said first substrate;

a first channel forming region formed between said first source and drain regions;

a first gate insulating region formed adjacent to said first source and drain regions and said first channel forming region; and

a first gate electrode formed adjacent to said first gate insulating film,

wherein said n-channel thin film transistor comprises:

a third source region and a third drain region formed over said first substrate;

a third channel forming region formed between said third source and drain regions;

a third gate insulating region formed adjacent to said third source and drain regions and said third channel forming region; and

a third gate electrode formed adjacent to said third gate insulating film, and

wherein said second p-channel thin film transistor comprises:

a second source region and a second drain region formed over said first substrate;

a second channel forming region formed between said second source and drain regions;

a second gate insulating region formed adjacent to said second source and drain regions and said second channel forming region; and

a second gate electrode formed adjacent to said second gate insulating film,

wherein a light blocking film is formed over said second gate electrode,

wherein a first pair of high concentration impurity regions formed between said first source and said first channel forming region and between said first channel forming region and said first drain region;

a pair of low concentration impurity regions formed between said third source and said third channel forming region and between said third channel forming region and said third drain region; and

a second pair of high concentration impurity regions formed between said second source and said second channel forming region and between said second channel forming region and said second drain region.

Claim 17 (Canceled)

Claim 18 (Previously Presented): A device according to claim 16 wherein said shift register circuit comprises at least a clocked inverter and an inverter.

Claims 19 and 20 (Canceled)

Claim 21 (Previously Presented): A device according to claim 16 further comprising a liquid crystal material injected between the first substrate and the second substrate.

Claim 22 (New): A display device comprising:
a pair of substrates;
an active matrix circuit and a driver circuit provided on one of the pair of the substrates;
a sealing member formed so as to cover the driver circuit, the sealing member being capable of light blocking; and
an orientating film formed on said sealing member,
wherein said sealing member comprises a pigment for light blocking; and
said sealing member is not in contact with said one of the pair of the substrates.

Claim 23 (New): A display device according to claim 22,
wherein the active matrix circuit has pixels arranged in a matrix form; and

regions in each of the pixels where source lines and drain lines overlap with a pixel electrode form a black matrix.

Claim 24 (New): A display device according to claim 22,
wherein one of an electrode or a wiring line connected to a source or drain of a thin-film transistor formed in the active matrix circuit is one of a metal film, a semiconductor film, and a silicide film, and

wherein a light blocking film for the thin-film transistor is formed by using the one of the metal film, the semiconductor film, and the silicide film.

Claim 25 (New): A display device according to claim 22 wherein said pair of the substrates are glass substrates or quartz substrates.

Claim 26 (New): A display device according to claim 22 wherein said pair of the substrates are bonded to each other with the sealing member.

Claim 27 (New): A device according to claim 22 further comprising:
at least a CMOS transistor formed in the driver circuit region, said CMOS transistor having an n-channel thin film transistor and a p-channel thin film transistor; and
a thin film transistor formed in each pixel in the active matrix circuit, said thin film transistor having at least an active layer, a gate insulating film adjacent to said active layer, a gate electrode adjacent to said gate insulating film,
wherein a light block film is formed over said gate electrode.

Claim 28 (New): A device according to claim 22 further comprising a liquid crystal material interposed between the pair of substrates,
wherein said sealing member seals the liquid crystal material.

Claim 29 (New): An electronic device comprising:
at least a first substrate and a second substrate;
a driver circuit region formed on said first substrate, said driver circuit region having at least one of a shift register circuit, a NAND circuit, a level shifter circuit and a buffer circuit;
an active matrix region formed on said first substrate, said active matrix region having at least a pixel;
a sealing member formed between said first and second substrates, said sealing member bonding said first and second substrates and covering said driver circuit region; and
an orientating film formed on said sealing member,
wherein said sealing member shields said driver circuit region from light;
said sealing member comprises a pigment for light blocking; and
said sealing member is not in contact with said one of the pair of the substrates.

Claim 30 (New): A device according to claim 29 wherein said shift register circuit comprises at least a clocked inverter and an inverter.

Claim 31 (New): A device according to claim 29 further comprising:
at least a CMOS transistor formed in said driver circuit region, said CMOS transistor having an n-channel thin film transistor and a p-channel thin film transistor; and
a thin film transistor formed in said pixel, said thin film transistor having at least an active layer, a gate insulating film adjacent to said active layer, a gate electrode adjacent to said gate insulating film, and further comprising a light blocking film formed over said gate electrode.

Claim 32 (New): A device according to claim 29 further comprising a liquid crystal material injected between the first substrate and the second substrate.

Claim 33 (New): A device according to claim 1 further comprising an interlayer insulating film made of a resin between said driver circuit and said sealing material.

Claim 34 (New): A device according to claim 8 further comprising an interlayer insulating film made of a resin between said driver circuit and said sealing material.

Claim 35 (New): A device according to claim 16 further comprising an interlayer insulating film made of a resin between said driver circuit and said sealing material.

Claim 36 (New): A device according to claim 22 further comprising an interlayer insulating film made of a resin between said driver circuit and said sealing material.

Claim 37 (New): A device according to claim 29 further comprising an interlayer insulating film made of a resin between said driver circuit and said sealing material.